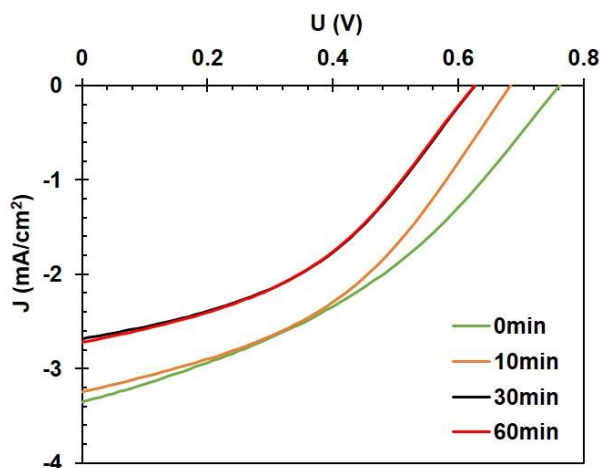


# Supplementary Materials: Silicon Phthalocyanines as Acceptor Candidates in Mixed Solution/Evaporation Processed Planar Heterojunction Organic Photovoltaic Devices

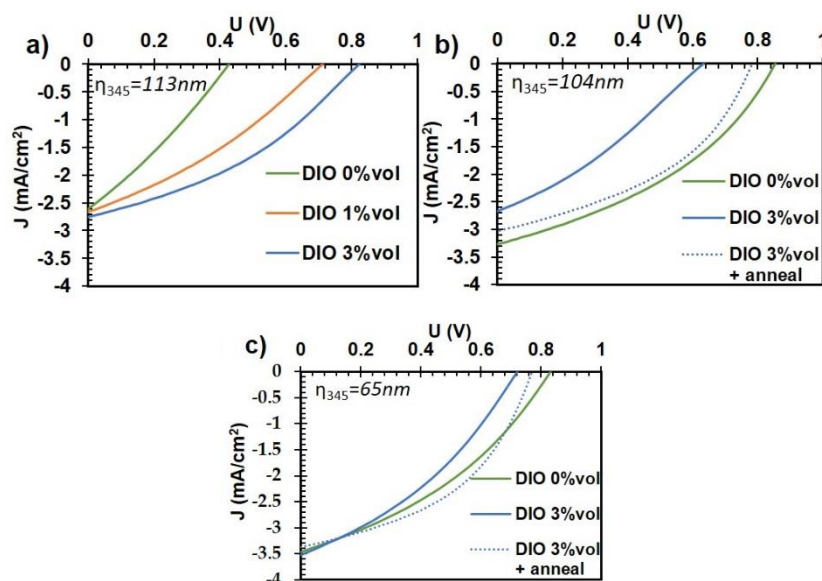
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**Figure S1.** Characteristic current vs. voltage (J-V) for PHJ OPV devices where the active layer is PCDTBT/(345F)<sub>2</sub>-SiPc (50 nm) and where the PCDTBT layer have been annealed at 150 °C for 0, 10, 30 and 60 min.



**Figure 2.** Characteristic current vs. voltage (J-V) for PHJ PCDTBT/(345F)<sub>2</sub>-SiPc devices with a SiPc thickness of **(a)** 113nm with incorporated DIO in the PCDTBT layer at 0, 1 and 3 vol %, **(b)** 104 nm and **(c)** 65 nm where DIO have been incorporated in the PCDTBT layer at 0, 3 and 3 vol % followed by annealing at 100 °C for 15 min.



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